L Number	Hits	Search Text	DB	Time stamp
-	69	breakdown adj phenom$4 NEAR5 dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/02 13:55
-	1	"breakdown phenomena" near5 "ultra-thin dielectric layer"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/02 11:14
-	214	"breakdown phenomena"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/02 14:36
-	54	"ultra-thin dielectric layer"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/02 14:41
-	12	"breakdown phenomena" and " memory device"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/02 11:14
-	4	(("6671040") or ("6667902")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/02 11:14
-	14	BREAKDOWN ADJ PHENOMENA ADJ ULTRA-THIN ADJ DIELECTRIC	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/02 11:14
-	2	"20030063518"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/02 11:14
-	69	(breakdown or (breask adj1 down)) adj phenom$4 NEAR5 dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/02 11:14
-	7	"breakdown phenomena" and "ultra-thin dielectric layer"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/02 11:59
-	2	("6700151").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/02 11:14
-	9	"ultra-thin dielectric layer" and breakdown adj phenom$9	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/02 11:14
-	4	"breakdown phenomena" and "semiconductor memory device"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/02 11:14
-	1	"ultra-thin dielectric layer" and " memory device"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/02 11:14
-	4	(("6671040") or ("6667902")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/02 11:14
-	2	"20040008538"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/02 11:59

-	2	("6215140").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/02 14:10
-	2	("4037243").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/02 14:34
-	31986	programmable adj1 read adj1only adj1 memory	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/02 14:40
-	20955	programmable adj1 read adj1only adj1 memory	USPAT	2004/03/02 14:36
-	9	(programmable adj1 read adj1only adj1 memory) and "breakdown phenomena"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/02 14:52
-	31557	"programmable read only memory"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/02 14:40
-	20695	"programmable read only memory"	USPAT	2004/03/02 14:41
-	3	"programmable read only memory" and "ultra-thin dielectric layer"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/02 14:41
-	2	"20030071296"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/02 14:52
-	4	"20030071296" or "20030071315"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/02 15:34
-	2	("6700151").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/02 15:34
-	6	("20030071296" or "20030071315") or (("6700151").PN.)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/03 06:37
-	3	("6700151").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/03 07:38